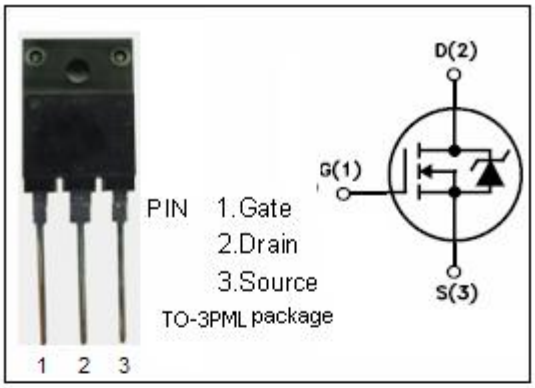
isc N-Channel MOSFET Transistor IRFS350A

FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area



DESCRIPTION

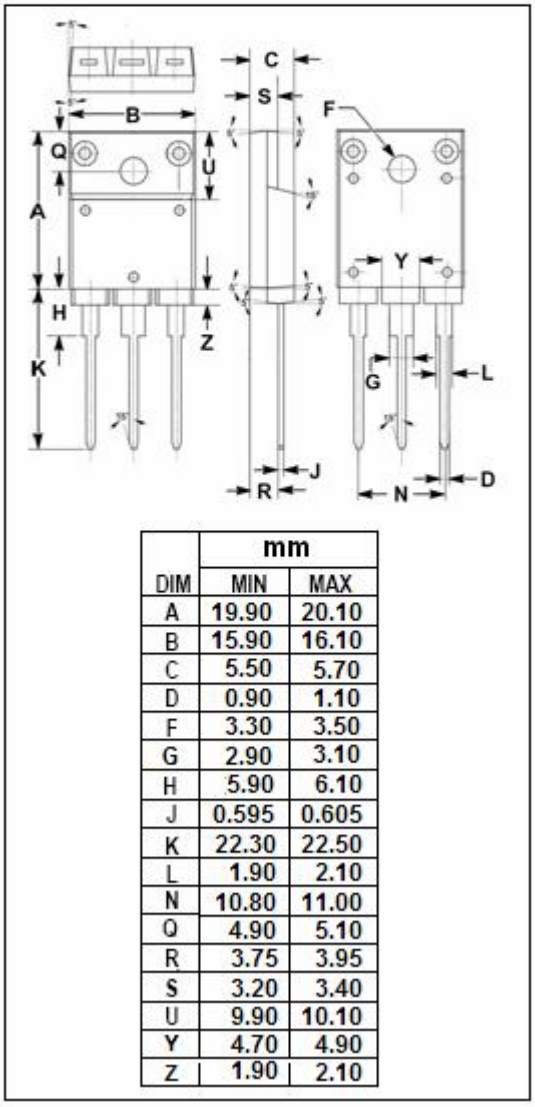
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	400	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous	11.5	A
I_{DM}	Drain Current-Single Pluse	68	A
P_D	Total Dissipation @T_C=25℃	92	W
T_J	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.35	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	40	℃/W



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	400		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 0.25mA	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=5.75A		0.3	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 400V; V_{GS}= 0 V_{DS}= 320V; V_{GS}= 0; T_j= 125℃		10 100	μA
V_{SD}	Forward On-Voltage	I_S= 11.5A; V_{GS}= 0		1.5	V

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